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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

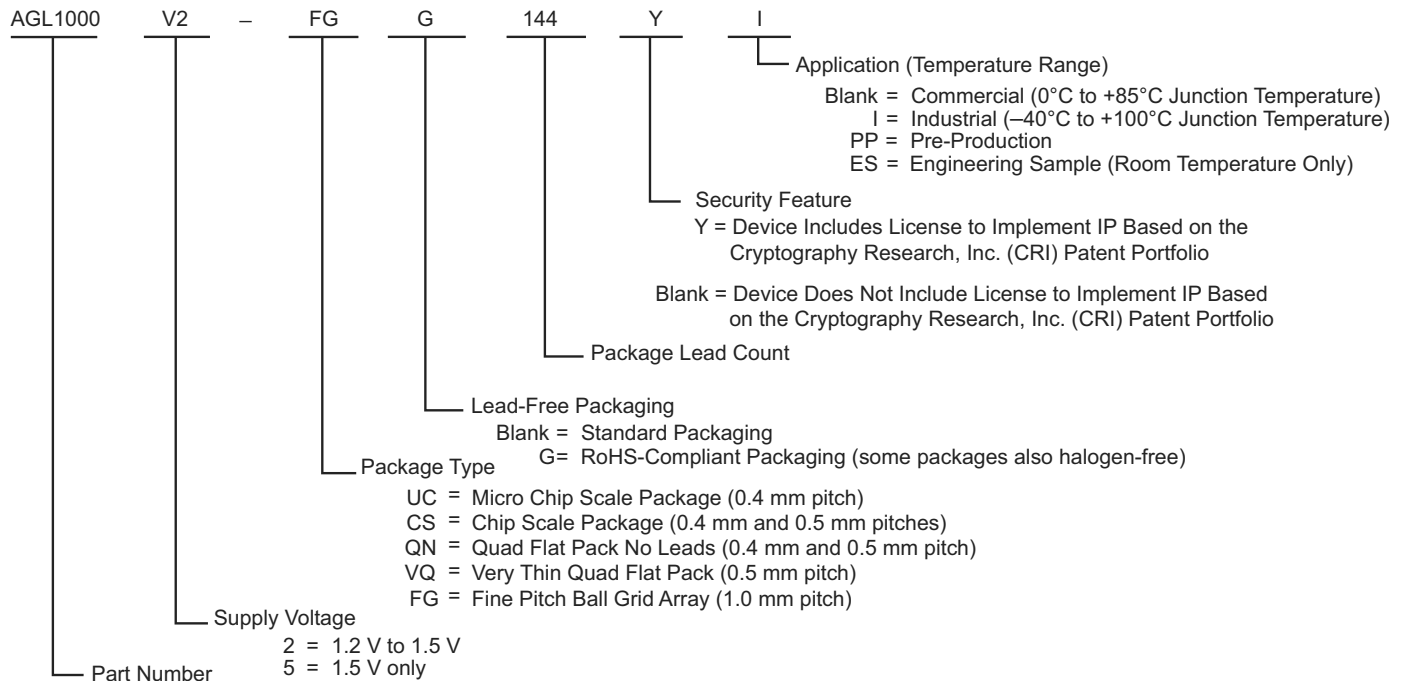
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	24576
Total RAM Bits	147456
Number of I/O	177
Number of Gates	1000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl1000v2-fgg256i

IGLOO Ordering Information



IGLOO Devices

AGL015 = 15,000 System Gates
AGL030 = 30,000 System Gates
AGL060 = 60,000 System Gates
AGL125 = 125,000 System Gates
AGL250 = 250,000 System Gates
AGL400 = 400,000 System Gates
AGL600 = 600,000 System Gates
AGL1000 = 1,000,000 System Gates

IGLOO Devices with Cortex-M1

M1AGL250 = 250,000 System Gates
M1AGL600 = 600,000 System Gates
M1AGL1000 = 1,000,000 System Gates

Note: Marking Information: IGLOO V2 devices do not have V2 marking, but IGLOO V5 devices are marked accordingly.

**Table 2-27 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings
Applicable to Standard I/O Banks**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ²	Slew Rate	V _{IL}		V _{IH}		V _{OL}	V _{OH}	I _{OL} ¹	I _{OH} ¹
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8 mA	High	−0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range ³	100 μ A	8 mA	High	−0.3	0.8	2	3.6	0.2	VDD-0.2	0.1	0.1
2.5 V LVCMOS	8 mA	8 mA	High	−0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS ⁴	1 mA	1 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range ^{4,5}	100 μ A	1 mA	High	−0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI − 0.1	0.1	0.1

Notes:

1. Currents are measured at 85°C junction temperature.
2. The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
4. Applicable to V2 Devices operating at VCCI $\geq$ VCC.
5. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.

Table 2-44 • I/O Short Currents IOSH/IOSL
Applicable to Standard I/O Banks

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
3.3 V LVCMOS Wide Range	100 μ A	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
1.5 V LVCMOS	2 mA	13	16
1.2 V LVCMOS	1 mA	20	26
1.2 V LVCMOS Wide Range	100 μ A	20	26

Note: * $T_J = 100^\circ\text{C}$

The length of time an I/O can withstand I_{OSH}/I_{OSL} events depends on the junction temperature. The reliability data below is based on a 3.3 V, 12 mA I/O setting, which is the worst case for this type of analysis.

For example, at 100°C , the short current condition would have to be sustained for more than six months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

Table 2-45 • Duration of Short Circuit Event before Failure

Temperature	Time before Failure
-40°C	> 20 years
-20°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years
85°C	2 years
100°C	6 months

Table 2-46 • I/O Input Rise Time, Fall Time, and Related I/O Reliability¹

Input Buffer	Input Rise/Fall Time (min.)	Input Rise/Fall Time (max.)	Reliability
LVTTTL/LVCMOS	No requirement	10 ns *	20 years (100°C)
LVDS/B-LVDS/M-LVDS/ LVPECL	No requirement	10 ns *	10 years (100°C)

Note: The maximum input rise/fall time is related to the noise induced into the input buffer trace. If the noise is low, then the rise time and fall time of input buffers can be increased beyond the maximum value. The longer the rise/fall times, the more susceptible the input signal is to the board noise. Microsemi recommends signal integrity evaluation/characterization of the system to ensure that there is no excessive noise coupling into input signals.

Table 2-60 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	2.89	0.26	0.97	1.10	2.93	2.38	2.53	2.96	8.72	8.17	ns
4 mA	Std.	1.55	2.89	0.26	0.97	1.10	2.93	2.38	2.53	2.96	8.72	8.17	ns
6 mA	Std.	1.55	2.50	0.26	0.97	1.10	2.54	2.04	2.77	3.37	8.33	7.82	ns
8 mA	Std.	1.55	2.50	0.26	0.97	1.10	2.54	2.04	2.77	3.37	8.33	7.82	ns
12 mA	Std.	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns
16 mA	Std.	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-61 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	4.39	0.26	0.94	1.10	4.46	3.91	2.17	2.44	ns
4 mA	Std.	1.55	4.39	0.26	0.94	1.10	4.46	3.91	2.17	2.44	ns
6 mA	Std.	1.55	3.72	0.26	0.94	1.10	3.78	3.43	2.40	2.85	ns
8 mA	Std.	1.55	3.72	0.26	0.94	1.10	3.78	3.43	2.40	2.85	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-62 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	2.74	0.26	0.94	1.10	2.78	2.26	2.17	2.55	ns
4 mA	Std.	1.55	2.74	0.26	0.94	1.10	2.78	2.26	2.17	2.55	ns
6 mA	Std.	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns
8 mA	Std.	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Timing Characteristics*Applies to 1.5 V DC Core Voltage***Table 2-83 • 2.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage****Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V****Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	4.96	0.18	1.08	0.66	5.06	4.59	2.26	2.00	8.66	8.19	ns
4 mA	Std.	0.97	4.96	0.18	1.08	0.66	5.06	4.59	2.26	2.00	8.66	8.19	ns
6 mA	Std.	0.97	4.15	0.18	1.08	0.66	4.24	3.94	2.54	2.51	7.83	7.53	ns
8 mA	Std.	0.97	4.15	0.18	1.08	0.66	4.24	3.94	2.54	2.51	7.83	7.53	ns
12 mA	Std.	0.97	3.57	0.18	1.08	0.66	3.65	3.47	2.73	2.84	7.24	7.06	ns
16 mA	Std.	0.97	3.39	0.18	1.08	0.66	3.46	3.36	2.78	2.92	7.06	6.95	ns
24 mA	Std.	0.97	3.38	0.18	1.08	0.66	3.38	3.38	2.83	3.25	6.98	6.98	ns

*Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.***Table 2-84 • 2.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage****Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V****Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.77	0.18	1.08	0.66	2.83	2.60	2.26	2.08	6.42	6.19	ns
4 mA	Std.	0.97	2.77	0.18	1.08	0.66	2.83	2.60	2.26	2.08	6.42	6.19	ns
6 mA	Std.	0.97	2.34	0.18	1.08	0.66	2.39	2.08	2.54	2.60	5.99	5.68	ns
8 mA	Std.	0.97	2.34	0.18	1.08	0.66	2.39	2.08	2.54	2.60	5.99	5.68	ns
12 mA	Std.	0.97	2.09	0.18	1.08	0.66	2.14	1.83	2.73	2.93	5.73	5.43	ns
16 mA	Std.	0.97	2.05	0.18	1.08	0.66	2.09	1.78	2.78	3.02	5.69	5.38	ns
24 mA	Std.	0.97	2.06	0.18	1.08	0.66	2.10	1.72	2.83	3.35	5.70	5.32	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-85 • 2.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	4.42	0.18	1.08	0.66	4.51	4.10	1.96	1.85	8.10	7.69	ns
4 mA	Std.	0.97	4.42	0.18	1.08	0.66	4.51	4.10	1.96	1.85	8.10	7.69	ns
6 mA	Std.	0.97	3.62	0.18	1.08	0.66	3.70	3.52	2.21	2.32	7.29	7.11	ns
8 mA	Std.	0.97	3.62	0.18	1.08	0.66	3.70	3.52	2.21	2.32	7.29	7.11	ns
12 mA	Std.	0.97	3.09	0.18	1.08	0.66	3.15	3.09	2.39	2.61	6.74	6.68	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-107 • 1.8 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	6.32	0.26	1.11	1.10	6.43	5.81	2.47	2.16	12.22	11.60	ns
4 mA	Std.	1.55	5.27	0.26	1.11	1.10	5.35	5.01	2.78	2.92	11.14	10.79	ns
6 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns
8 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-108 • 1.8 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.11	1.10	3.26	3.18	2.47	2.20	9.05	8.97	ns
4 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.75	2.50	2.78	3.01	8.54	8.29	ns
6 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns
8 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-109 • 1.8 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	6.13	0.26	1.08	1.10	6.24	5.79	2.08	1.78	ns
4 mA	Std.	1.55	5.17	0.26	1.08	1.10	5.26	4.98	2.38	2.54	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-110 • 1.8 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	3.06	0.26	1.08	1.10	3.10	3.01	2.08	1.83	3.06	ns
4 mA	Std.	2.60	0.26	1.08	1.10	2.64	2.33	2.38	2.62	2.60	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-119 • 1.5 V LVC MOS Low Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	5.88	0.18	1.14	0.66	6.00	5.45	2.00	1.94	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-120 • 1.5 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	2.51	0.18	1.14	0.66	2.56	2.21	1.99	2.03	ns

Notes:

- Software default selection highlighted in gray.
- For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage**Table 2-121 • 1.5 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage****Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	7.17	0.26	1.27	1.10	7.29	6.60	3.33	3.03	13.07	12.39	ns
4 mA	Std.	1.55	6.27	0.26	1.27	1.10	6.37	5.86	3.61	3.51	12.16	11.64	ns
6 mA	Std.	1.55	5.94	0.26	1.27	1.10	6.04	5.70	3.67	3.64	11.82	11.48	ns
8 mA	Std.	1.55	5.86	0.26	1.27	1.10	5.96	5.71	2.83	4.11	11.74	11.50	ns
12 mA	Std.	1.55	5.86	0.26	1.27	1.10	5.96	5.71	2.83	4.11	11.74	11.50	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-122 • 1.5 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V****Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.44	0.26	1.27	1.10	3.49	3.35	3.32	3.12	9.28	9.14	ns
4 mA	Std.	1.55	3.06	0.26	1.27	1.10	3.10	2.89	3.60	3.61	8.89	8.67	ns
6 mA	Std.	1.55	2.98	0.26	1.27	1.10	3.02	2.80	3.66	3.74	8.81	8.58	ns
8 mA	Std.	1.55	2.96	0.26	1.27	1.10	3.00	2.70	3.75	4.23	8.78	8.48	ns
12 mA	Std.	1.55	2.96	0.26	1.27	1.10	3.00	2.70	3.75	4.23	8.78	8.48	ns

Notes:

- Software default selection highlighted in gray.
- For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-138 • Minimum and Maximum DC Input and Output Levels for LVCMOS 1.2 V Wide Range
Applicable to Standard Plus I/O Banks

1.2 V LVCMOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Equivalent Software Default Drive Strength Option ¹	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ⁴	Max. mA ⁴	μA ⁵	μA ⁵
100 μA	2mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	100	100	20	26	10	10

Notes:

1. The minimum drive strength for the default LVCMOS 1.2 V software configuration when run in wide range is $\pm 100 \mu\text{A}$. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3 \text{ V} < V_{\text{IN}} < V_{\text{IL}}$.
3. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{\text{IH}} < V_{\text{IN}} < V_{\text{CCI}}$. Input current is larger when operating outside recommended ranges
4. Currents are measured at 100°C junction temperature and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

Table 2-139 • Minimum and Maximum DC Input and Output Levels for LVCMOS 1.2 V Wide Range
Applicable to Standard I/O Banks

1.2 V LVCMOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Equivalent Software Default Drive Strength Option ¹	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ⁴	Max. mA ⁴	μA ⁵	μA ⁵
100 μA	1 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	100	100	20	26	10	10

Notes:

1. The minimum drive strength for the default LVCMOS 1.2 V software configuration when run in wide range is $\pm 100 \mu\text{A}$. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3 \text{ V} < V_{\text{IN}} < V_{\text{IL}}$.
3. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{\text{IH}} < V_{\text{IN}} < V_{\text{CCI}}$. Input current is larger when operating outside recommended ranges
4. Currents are measured at 100°C junction temperature and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

Table 2-140 • 1.2 V LVCMOS Wide Range AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.2	0.6	5

Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.

Timing Characteristics

Refer to LVCMOS 1.2 V (normal range) "Timing Characteristics" on page 2-75 for worst-case timing.

Output DDR Module

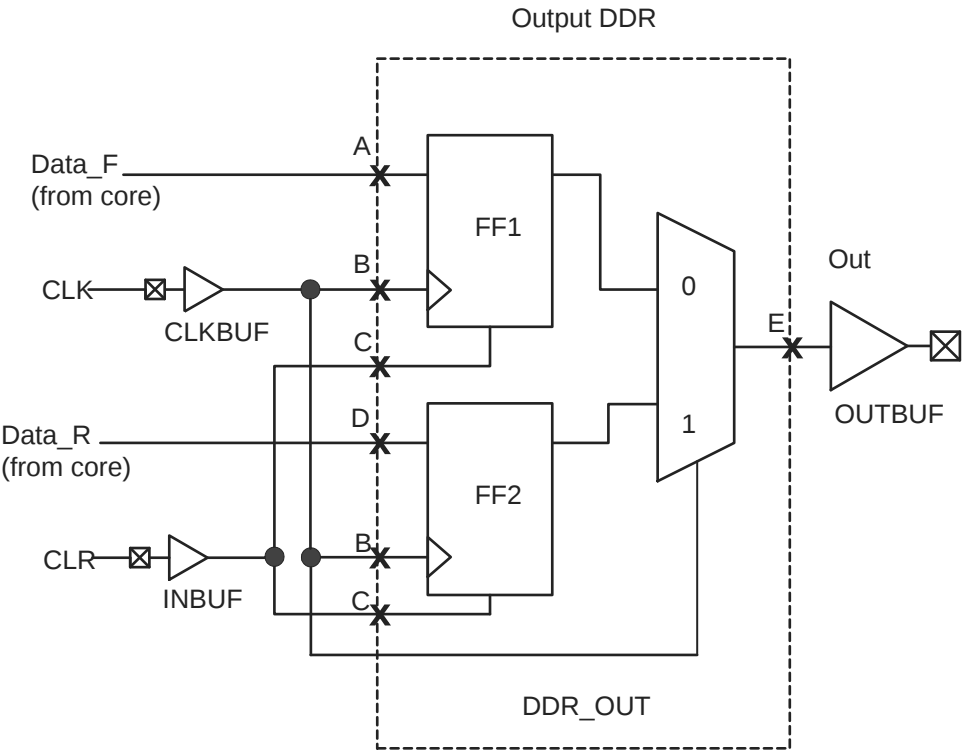


Figure 2-23 • Output DDR Timing Model

Table 2-166 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t _{DDROCLKQ}	Clock-to-Out	B, E
t _{DDROCLR2Q}	Asynchronous Clear-to-Out	C, E
t _{DDROREMCLR}	Clear Removal	C, B
t _{DDRORECCLR}	Clear Recovery	C, B
t _{DDROSUD1}	Data Setup Data_F	A, B
t _{DDROSUD2}	Data Setup Data_R	D, B
t _{DDROHD1}	Data Hold Data_F	A, B
t _{DDROHD2}	Data Hold Data_R	D, B

1.2 V DC Core Voltage**Table 2-168 • Output DDR Propagation Delays****Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	1.60	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	1.09	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	1.16	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	1.99	ns
$t_{\text{DDROREMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{\text{DDRORECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.24	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.31	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	160.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-177 • AGL250 Global Resource**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.39	1.73	ns
t_{RCKH}	Input High Delay for Global Clock	1.41	1.84	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-178 • AGL400 Global Resource**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.45	1.79	ns
t_{RCKH}	Input High Delay for Global Clock	1.48	1.91	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage-supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-179 • AGL600 Global Resource**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.48	1.82	ns
t_{RCKH}	Input High Delay for Global Clock	1.52	1.94	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.42	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-180 • AGL1000 Global Resource**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$**

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.55	1.89	ns
t_{RCKH}	Input High Delay for Global Clock	1.60	2.02	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.42	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

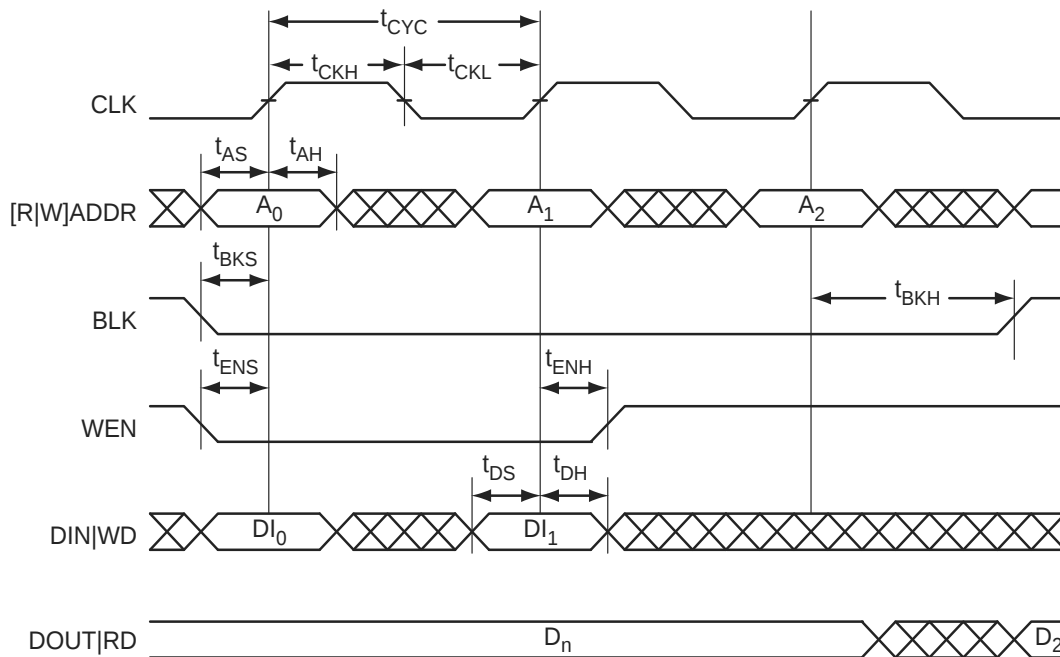


Figure 2-34 • RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.

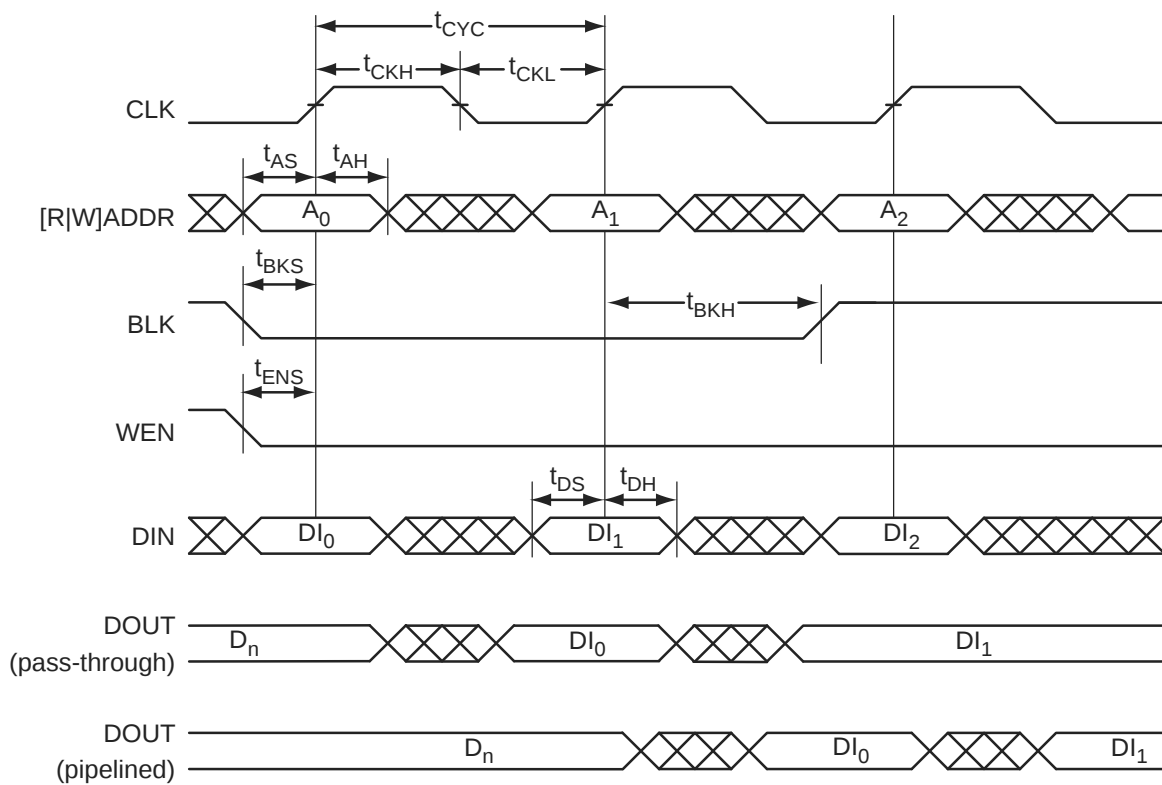


Figure 2-35 • RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 only.

Table 2-194 • RAM512X18**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.53	ns
t_{AH}	Address hold time	0.29	ns
t_{ENS}	REN, WEN setup time	1.36	ns
t_{ENH}	REN, WEN hold time	0.15	ns
t_{DS}	Input data (WD) setup time	1.33	ns
t_{DH}	Input data (WD) hold time	0.66	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	7.88	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	3.20	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.87	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	1.04	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow through)	3.86	ns
	RESET Low to data out Low on RD (pipelined)	3.86	ns
$t_{REMRSTB}$	RESET removal	1.12	ns
$t_{RECRSTB}$	RESET recovery	5.93	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

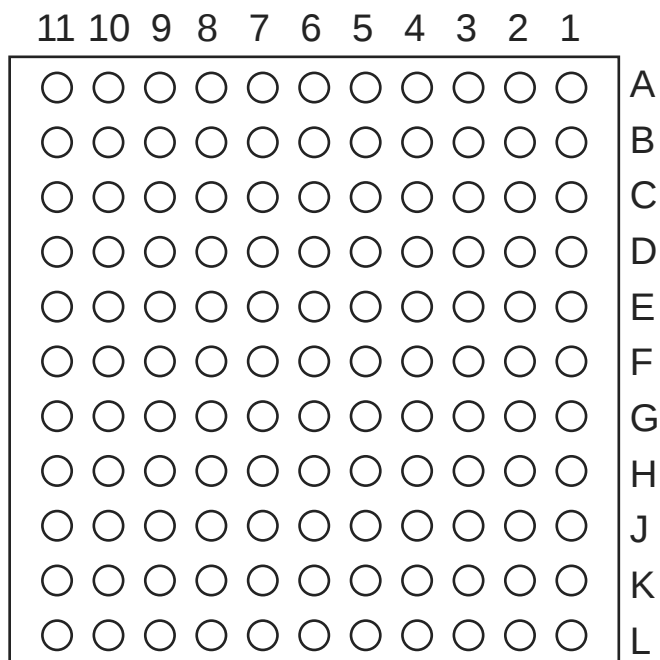
1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

UC81	
Pin Number	AGL030 Function
A1	IO00RSB0
A2	IO02RSB0
A3	IO06RSB0
A4	IO11RSB0
A5	IO16RSB0
A6	IO19RSB0
A7	IO22RSB0
A8	IO24RSB0
A9	IO26RSB0
B1	IO81RSB1
B2	IO04RSB0
B3	IO10RSB0
B4	IO13RSB0
B5	IO15RSB0
B6	IO20RSB0
B7	IO21RSB0
B8	IO28RSB0
B9	IO25RSB0
C1	IO79RSB1
C2	IO80RSB1
C3	IO08RSB0
C4	IO12RSB0
C5	IO17RSB0
C6	IO14RSB0
C7	IO18RSB0
C8	IO29RSB0
C9	IO27RSB0
D1	IO74RSB1
D2	IO76RSB1
D3	IO77RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	IO23RSB0
D8	IO31RSB0
D9	IO30RSB0

UC81	
Pin Number	AGL030 Function
E1	GEB0/IO71RSB1
E2	GEA0/IO72RSB1
E3	GEC0/IO73RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GDC0/IO32RSB0
E8	GDA0/IO33RSB0
E9	GDB0/IO34RSB0
F1	IO68RSB1
F2	IO67RSB1
F3	IO64RSB1
F4	GND
F5	VCCIB1
F6	IO47RSB1
F7	IO36RSB0
F8	IO38RSB0
F9	IO40RSB0
G1	IO65RSB1
G2	IO66RSB1
G3	IO57RSB1
G4	IO53RSB1
G5	IO49RSB1
G6	IO45RSB1
G7	IO46RSB1
G8	VJTAG
G9	TRST
H1	IO62RSB1
H2	FF/IO60RSB1
H3	IO58RSB1
H4	IO54RSB1
H5	IO48RSB1
H6	IO43RSB1
H7	IO42RSB1
H8	TDI
H9	TDO

UC81	
Pin Number	AGL030 Function
J1	IO63RSB1
J2	IO61RSB1
J3	IO59RSB1
J4	IO56RSB1
J5	IO52RSB1
J6	IO44RSB1
J7	TCK
J8	TMS
J9	VPUMP

CS121



Note: This is the bottom view of the package.

Note

For more information on package drawings, see PD3068: *Package Mechanical Drawings*.

CS281		CS281	
Pin Number	AGL600 Function	Pin Number	AGL600 Function
R15	IO94RSB2	V10	IO112RSB2
R16	GDA1/IO88PPB1	V11	IO110RSB2
R18	GDB0/IO87NPB1	V12	IO108RSB2
R19	GDC0/IO86NPB1	V13	IO102RSB2
T1	IO148PPB3	V14	GND
T2	GEC0/IO146NPB3	V15	IO93RSB2
T4	GEB0/IO145NPB3	V16	GDA2/IO89RSB2
T5	IO132RSB2	V17	TDI
T6	IO136RSB2	V18	VCCIB2
T7	IO130RSB2	V19	TDO
T8	IO126RSB2	W1	GND
T9	IO120RSB2	W2	FF/GEB2/IO142RSB2
T10	GND	W3	IO139RSB2
T11	IO113RSB2	W4	IO137RSB2
T12	IO104RSB2	W5	IO134RSB2
T13	IO101RSB2	W6	IO133RSB2
T14	IO98RSB2	W7	IO128RSB2
T15	GDC2/IO91RSB2	W8	IO124RSB2
T16	TMS	W9	IO119RSB2
T18	VJTAG	W10	VCCIB2
T19	GDB1/IO87PPB1	W11	IO109RSB2
U1	IO147PDB3	W12	IO107RSB2
U2	GEA1/IO144PPB3	W13	IO105RSB2
U6	IO131RSB2	W14	IO100RSB2
U14	IO99RSB2	W15	IO96RSB2
U18	TRST	W16	IO92RSB2
U19	GDA0/IO88NPB1	W17	GDB2/IO90RSB2
V1	IO147NDB3	W18	TCK
V2	VCCIB3	W19	GND
V3	GEC2/IO141RSB2		
V4	IO140RSB2		
V5	IO135RSB2		
V6	GND		
V7	IO125RSB2		
V8	IO122RSB2		
V9	IO116RSB2		

CS281	
Pin Number	AGL1000 Function
A1	GND
A2	GAB0/IO02RSB0
A3	GAC1/IO05RSB0
A4	IO13RSB0
A5	IO11RSB0
A6	IO16RSB0
A7	IO20RSB0
A8	IO24RSB0
A9	IO29RSB0
A10	VCCIB0
A11	IO39RSB0
A12	IO45RSB0
A13	IO48RSB0
A14	IO58RSB0
A15	IO61RSB0
A16	IO62RSB0
A17	GBC1/IO73RSB0
A18	GBA0/IO76RSB0
A19	GND
B1	GAA2/IO225PPB3
B2	VCCIB0
B3	GAB1/IO03RSB0
B4	GAC0/IO04RSB0
B5	IO12RSB0
B6	GND
B7	IO21RSB0
B8	IO26RSB0
B9	IO34RSB0
B10	IO35RSB0
B11	IO36RSB0
B12	IO46RSB0
B13	IO52RSB0
B14	GND
B15	IO59RSB0
B16	GBC0/IO72RSB0
B17	GBA1/IO77RSB0

CS281	
Pin Number	AGL1000 Function
B18	VCCIB1
B19	IO79NDB1
C1	GAB2/IO224PPB3
C2	IO225NPB3
C6	IO18RSB0
C14	IO63RSB0
C18	IO78NPB1
C19	GBB2/IO79PDB1
D1	IO219PPB3
D2	IO223NPB3
D4	GAA0/IO00RSB0
D5	GAA1/IO01RSB0
D6	IO15RSB0
D7	IO19RSB0
D8	IO27RSB0
D9	IO32RSB0
D10	GND
D11	IO38RSB0
D12	IO44RSB0
D13	IO47RSB0
D14	IO60RSB0
D15	GBB0/IO74RSB0
D16	GBA2/IO78PPB1
D18	GBC2/IO80PPB1
D19	IO88NPB1
E1	IO217NPB3
E2	IO221PPB3
E4	IO221NPB3
E5	IO10RSB0
E6	IO14RSB0
E7	IO25RSB0
E8	IO28RSB0
E9	IO31RSB0
E10	IO33RSB0
E11	IO42RSB0
E12	IO49RSB0

CS281	
Pin Number	AGL1000 Function
E13	IO53RSB0
E14	GBB1/IO75RSB0
E15	IO80NPB1
E16	IO85PPB1
E18	IO83PPB1
E19	IO84NPB1
F1	IO214NPB3
F2	GND
F3	IO217PPB3
F4	IO219NPB3
F5	IO224NPB3
F15	IO85NPB1
F16	IO84PPB1
F17	IO83NPB1
F18	GND
F19	IO90PPB1
G1	IO212NPB3
G2	IO211NDB3
G4	IO214PPB3
G5	IO212PPB3
G7	GAC2/IO223PPB3
G8	VCCIB0
G9	IO30RSB0
G10	IO37RSB0
G11	IO43RSB0
G12	VCCIB0
G13	IO88PPB1
G15	IO89NDB1
G16	IO89PDB1
G18	GCC0/IO91NPB1
G19	GCB1/IO92PPB1
H1	GFB0/IO208NPB3
H2	IO211PDB3
H4	GFC1/IO209PPB3
H5	GFB1/IO208PPB3
H7	VCCIB3

FG256	
Pin Number	AGL400 Function
H3	GFB1/IO146PPB3
H4	VCOMPLF
H5	GFC0/IO147NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO67NPB1
H13	GCB1/IO68PPB1
H14	GCA0/IO69NPB1
H15	NC
H16	GCB0/IO68NPB1
J1	GFA2/IO144PPB3
J2	GFA1/IO145PDB3
J3	VCCPLF
J4	IO143NDB3
J5	GFB2/IO143PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO71PPB1
J13	GCA1/IO69PPB1
J14	GCC2/IO72PPB1
J15	NC
J16	GCA2/IO70PDB1
K1	GFC2/IO142PDB3
K2	IO144NPB3
K3	IO141PPB3
K4	IO120RSB2
K5	VCCIB3
K6	VCC
K7	GND
K8	GND

FG256	
Pin Number	AGL400 Function
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO71NPB1
K14	IO74RSB1
K15	IO72NPB1
K16	IO70NDB1
L1	IO142NDB3
L2	IO141NPB3
L3	IO125RSB2
L4	IO139RSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO78VPB1
L14	IO76VDB1
L15	IO76UDB1
L16	IO75PDB1
M1	IO140PDB3
M2	IO130RSB2
M3	IO138NPB3
M4	GEC0/IO137NPB3
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO108RSB2
M9	IO101RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO83RSB2
M14	GDB1/IO78UPB1

FG256	
Pin Number	AGL400 Function
M15	GDC1/IO77UDB1
M16	IO75NDB1
N1	IO140NDB3
N2	IO138PPB3
N3	GEC1/IO137PPB3
N4	IO131RSB2
N5	GNDQ
N6	GEA2/IO134RSB2
N7	IO117RSB2
N8	IO111RSB2
N9	IO99RSB2
N10	IO94RSB2
N11	IO87RSB2
N12	GNDQ
N13	IO93RSB2
N14	VJTAG
N15	GDC0/IO77VDB1
N16	GDA1/IO79UDB1
P1	GEB1/IO136PDB3
P2	GEB0/IO136NDB3
P3	VMV2
P4	IO129RSB2
P5	IO128RSB2
P6	IO122RSB2
P7	IO115RSB2
P8	IO110RSB2
P9	IO98RSB2
P10	IO95RSB2
P11	IO88RSB2
P12	IO84RSB2
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO79VDB1
R1	GEA1/IO135PDB3
R2	GEA0/IO135NDB3
R3	IO127RSB2
R4	GEC2/IO132RSB2

FG484	
Pin Number	AGL600 Function
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO69PPB1
K17	IO65NPB1
K18	IO75PDB1
K19	IO75NDB1
K20	NC
K21	IO76NDB1
K22	IO76PDB1
L1	NC
L2	IO155PDB3
L3	NC
L4	GFB0/IO163NPB3
L5	GFA0/IO162NDB3
L6	GFB1/IO163PPB3
L7	VCOMPLF
L8	GFC0/IO164NPB3
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO69NPB1
L16	GCB1/IO70PPB1
L17	GCA0/IO71NPB1
L18	IO67NPB1
L19	GCB0/IO70NPB1
L20	IO77PDB1
L21	IO77NDB1
L22	IO78NPB1
M1	NC
M2	IO155NDB3